

Chip Select Maximum LOW Time – Industrial Plus Temperature	t_{CSM}	–	1.0	–	1.0	–	1.0	μs
RWDS Data Mask Valid	t_{DMV}	0	–	0	–	0	–	ns

Table 25. 3.0 V Write Timing Parameters

Parameter	Symbol	100 MHz		Unit
		Min	Max	
Read-Write Recovery Time	t_{RWR}	40	–	ns
Access Time	t_{ACC}	40	–	ns
Refresh Time	t_{RFH}	40	–	ns
Chip Select Maximum LOW Time – Industrial Temperature	t_{CSM}	–	4.0	μs
Chip Select Maximum LOW Time – Industrial Plus Temperature		–	1.0	μs
RWDS Data Mask Valid	t_{DMV}	0	–	ns

Note

84. Refer to Table 23 for parameters that are shown in the timing diagram but not listed in this table.

Figure 25. Write Timing Diagram — No Additional Latency

